

05/10/05

RELIABILITY REPORT FOR

DS1088L, Rev A3

Dallas Semiconductor

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Prepared by:

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Conclusion:

The following Reliability Test successfully meets the quality and reliability standards set forth by this special Temperature Cycle Evaluation:

DS1088L, Rev A3

Device Description:

A description of the device used in this qualification can be found in the product data sheet. You can find the product data sheet at http://dbserv.maxim-ic.com/l_datasheet3.cfm.

Reliability Derating:

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

AfT = exp((Ea/k)*(1/Tu - 1/Ts)) = tu/ts AfT = Acceleration factor due to Temperature tu = Time at use temperature (e.g. 55°C) ts = Time at stress temperature (e.g. 125°C) k = Boltzmann's Constant (8.617 x 10-5 eV/°K) Tu = Temperature at Use (°K) Ts = Temperature at Stress (°K) Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

 $AfV = exp(B^{*}(Vs - Vu))$

AfV = Acceleration factor due to Voltage

Vs = Stress Voltage (e.g. 7.0 volts)

Vu = Maximum Operating Voltage (e.g. 5.5 volts)

B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

Fr = X/(ts * AfV * AfT * N * 2)X = Chi-Sq statistical upper limit N = Life test sample size Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

MTTF = 1/Fr

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process/assembly is:

FAILURE RATE:	MTTF (YRS): 9048	FITS: 12.6
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The parameters used to calculate this failure rate are as follows:

Cf: 60%	Ea: 0.7	B: 0	Tu: 25 °C	Vu: 3.6 Volts
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The reliability data follows. A the start of this data is the device information. This is a description of the device for this report. Following this is the assembly information. This section includes a description of the assembly vehicle used to generate this reliability data for both qualifications and monitors. The next section is the detailed reliability data for each stress found in the qualification / monitor. If there are additional assemblies used as part of this report, a description of each will follow which includes the respective reliability data for that assembly. The reliability data section includes the latest data available.

Device Information:	
Device: Process: Passivation: Die Size: Number of Transistors: Interconnect: Gate Oxide Thickness:	DS1088L D35X-3P3M,DPE2,CrSi,DSD,PDESD,PDRES,Cap,ENPN,D Passivation w/Nov 4% Ox 51 x 52 4507 Aluminum / 1% Silicon / 0.5% Copper 131 Å
Assembly Information:	
Qualification Vehicle: Assembly Site: Pin Count: Package Type: Body Size: Mold Compound: Lead Frame: Lead Frame: Lead Finsh: Die Attach: Bond Wire / Size: Theta JA: Theta JC: Flammability: Moisture Sensitivity (JEDEC J-STD20A)	DS1088L ATP (Amkor, PI) 8 uSOP 3x0.85 Nitto MP8000 w/BCB4026 Die Coat Stamped Copper C7025 SnPb Plate 84-1 LMISR4 Epoxy Silverfilled Ablebond Au / 1.0 mil 221 39 UL 94-V0 Level 1
Date Code Range:	0501 to 0501

ELECTRICAL CHARACTERIZATION

DESCRIPTION	DATE CODE CONDITION		READPOINT		QTY	FAILS	FA#
ESD SENSITIVITY	0501	EOS/ESD S5.1 HBM 500 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0501	EOS/ESD S5.1 HBM 1000 VOLTS	1	PUL'S	3	0	
ESD SENSITIVITY	0501	EOS/ESD S5.1 HBM 2000 VOLTS	1	PUL'S	3	0	

ESD SENSITIVITY	0501	EOS/ESD S5.1 HBM 4000 VOLTS		1	PUL'S	3	0	
ESD SENSITIVITY	0501	EOS/ESD S5.1 HBM 8000 VOLTS		1	PUL'S	3	3	No FA
LATCH-UP	0501	JESD78, I-TEST 125C		2	DYS	6	0	
LATCH-UP	0501	JESD78, Vsupply TEST 125C		2	DYS	6	0	
					Total:		3	
OPERATING LIFE								
DESCRIPTION	DATE CODE CONDITION		READPOINT		QTY	FAILS	FA#	
HIGH TEMP OP LIFE	0501	125C, 3.6 VOLTS		1000 HRS		77	0	
					Total:		0	
PRECONDITIONING L	EVEL 1							
DESCRIPTION	DATE COD	ECONDITION		READPOINT		QTY	FAILS	FA#
STORAGE LIFE	0501	125C		24	HRS	306		
MOISTURE SOAK		85 C/85% R.H.		168	HRS	306		
CONVECTION REFLOW		235C +5/-0C		3	PASS	306	0	
					Total:		0	
STORAGE LIFE								
DESCRIPTION	DATE COD	DATE CODE CONDITION		REA	DPOINT	QTY	FAILS	FA#
STORAGE LIFE	0501	150C		1000	HRS	77	0	
					Total:		0	
TEMPERATURE CYC	LE							
DESCRIPTION	DATE COD	E CONDITION		READPOINT		QTY	FAILS	FA#
TEMP CYCLE	0501	-55C TO 125C		1000) CYS	77	0	
					Total:		0	
UNBIASED MOISTUR	E RESISTA	NCE						
DESCRIPTION	DATE COD	E CONDITION		REA	DPOINT	QTY	FAILS	FA#
AUTOCLAVE	0501	121C, 2 ATM STEAM, UNBIASED		168	HRS	70	0	
					Total:		0	
FAILURE RATE:	МТ	TF (YRS): 9048	FITS:	12.6	5			